

A1 JP, H03-197640, A.

Title of the invention

A tantalum material having a high degree of purity, a method for preparing said tantalum material, and a tantalum target thereof.

The scope of the claim

1. A tantalum material having a high degree of purity characterized in that oxygen is contained in an amount of no greater than 50 ppm, and that each of iron, nickel and chromium is contained in an amount of no greater than 0.05 ppm.
2. A method for preparing a tantalum material having a high degree of purity of claim 1, characterized in that the tantalum material is purified by iodide decomposition, and is subsequently melted in a vacuum under a pressure no higher than 5×10^{-5} mbar.
3. A method for preparing a tantalum material having a high degree of purity according to claim 2, characterized in that the tantalum material is melted by using an electron-beam.
4. A tantalum target prepared with a tantalum material of claim 1.